

# GigaDevice Semiconductor Inc.

# GD30WS8815x PMIC for TWS Headset Charging Box

**Datasheet** 



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#### 1 Features

- Extreme low quiescent current, <5µA in sleep mode
- Charging features
  - Switching charging up to 1.5A maximum current programmable through ISET
  - Full charge cycle: pre-charge, constant current/constant voltage, trickle charge
  - Charging current and trickle charging current are all programmable through I2C
  - Support variety of battery chemistries, 4.1/4.2/4.3/4.35/4.4V @0.5%
- Boost converter
  - Support up to 1A load current
  - High efficiency synchronous boost converter @95%
  - Output current limit programmable through I2C, 1.6A/1.8A/2.0A/2.2A
- Power path management
  - Power path management allows simultaneous battery charging and system supply,
     system discharge priority
  - When the system load increases, the charging current is reduced dynamically according to the input current and system voltage
  - USB current limit programmable through I2C, -5%/0%/5%/10% @IcccH + 0.5A
     (Maximum current 3A)
  - Over voltage protection up to 5.6V, V<sub>SYS</sub> voltage regulation limit: 4.6V
- Protection features
  - Short Circuit Protection Input
  - Over Voltage/Current Protection
  - Over/Under temperature protection
  - Boost Over voltage (OV) during charge @5.5V
  - Boost Under voltage (UV) when charge/discharge @4.3V
- Additional features
  - 3.3V LDO support 80mA
  - Programmable LED driver
  - Low external component count
  - Simple I<sup>2</sup>C compatible interface

## 2 Applications

- TWS earbuds charging case
- Headsets and hearing aids
- Low battery applications such as smart watches and fitness accessories
- Patient monitors and portable medical equipment



## 3 General description

The GD30WS8815x is a highly integrated, programmable, low quiescent current power management integrated circuit (PMIC) that integrates the most common needs for wearables and low power battery applications.

The GD30WS8815x integrates a switching charger of programmable charging current (up to 1.5A) and a synchronous boost converter at fixed 5V output. The IC also includes a 12-bit ADC for battery gauge monitoring, and a low quiescent current, low noise LDO capable of delivering 80mA load current.

The device integrates advanced power path management and control that allow the device to provide power to the system while charging the battery even with poor adapters. The dynamic power path management automatically balances the currents delivered to the system and battery charging. A high voltage and over current protection circuit is implemented in the IC to protect it from high input voltage as high as 20V.

The GD30WS8815x device supports charge current up to 1.5A and termination current down to 5mA. The maximum charge current is set at a default of 1.5A and is programmable by connecting an external resistor from ISET pin to ground. The battery is charged using a standard Li-Ion charge profile with three phases: pre-charge, constant current and constant voltage regulation.

The device has several power saving modes to increase battery life whether the product is in storage or in operation. The quiescent current could be as low as 5uA when it is in sleep mode and thus most battery could sustain more than a year in shelf.

The versatile features of GD30WS8815x allow for it to best used in wearable applications such as headsets, earbuds and hearing aids, or low battery applications such as smart watches and fitness accessories, or patient monitors and portable medical equipment.



#### 4 Device overview

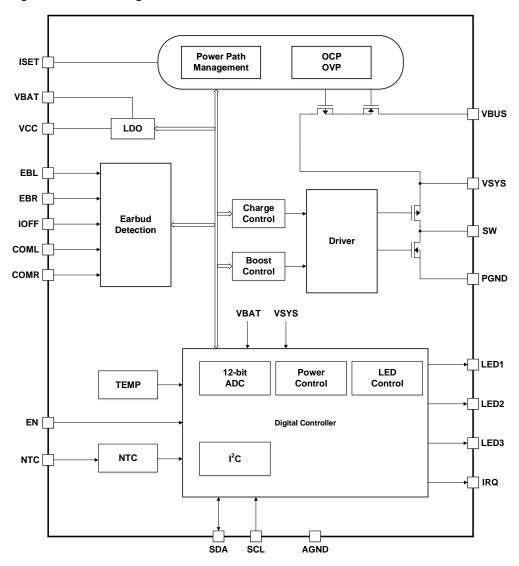
#### 4.1 Device information

Table 4-1 Device information for GD30WS8815x

Part Number	Package	Function	Description
GD30WS8815x	OENI24(4V4)	MCU version	Cooperate with MCU solution,
GD30W30013X	QFN24(4X4)	WICO VEISION	supports EN enable control

# 4.2 Block diagram

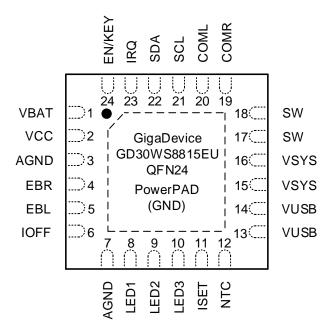
Figure 4-1 Block diagram for GD30WS8815x





## 4.3 Pinout and pin assignment

Figure 4-2 GD30WS8815x QFN24 pinouts



#### 4.4 Pin definitions

Table 4-2 GD30WS8815x QFN24 pin definitions

Pin Name	Pins	Pin Type	Functions description	
VBAT	1	Р	Connect to positive node of a battery.	
VCC	2	Р	LDO output voltage, connect a capacitor to ground.	
AGND	3	G	Ground.	
EBR	4	I/O	Positive terminal for right earbud.	
EBL	5	I/O	Positive terminal for left earbud.	
IOFF	6	I	Set the termination current for BOOST.	
AGND	7	G	Ground.	
LED1	8	0	.ED driver #1 for battery gauge monitor or other.	
LED2	9	0	LED driver #2 for battery gauge monitor or other.	
LED3	10	O LED driver #3 for battery gauge monitor or other.		
ISET	11	I	Set the charge current by connecting a resistor to ground.	
NTC	12	I	Thermistor terminal voltage for battery, or pull high to DISABLE the IC.	
VUSB	13,14	Р	Power input from USB or 5V voltage source.	



VSYS	15,16	Р	Output of boost converter or system voltage.	
SW	17,18	Р	Switching node, connecting to VBAT by an inductor.	
COMR	19	I/O	Right earbud communication input and output.	
COML	20	I/O	Left earbud communication input and output.	
SCL	21	I	I2C communication to the host controller, clock.	
SDA	22	I/O	I2C communication to the host controller, data.	
IRQ	23 O Interrupt output.		Interrupt output.	
EN	24	I	IC enable.	
PGND	EPAD	G	Device power ground.	

#### Notes:

1. Type: I = input, O = output, I/O = input or output, P = power, G = Ground.

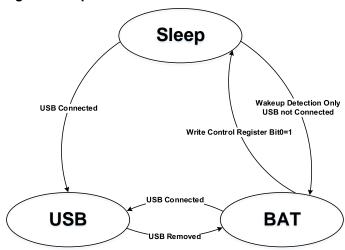


# 5 Functional description

#### 5.1 Operation modes

The GD30WS8815x IC has three different operation modes: Sleep, Battery and USB operation mode, as shown in Figure 5-1.

Figure 5-1 Operation modes



#### 5.2 Battery charging

#### **5.2.1** Battery charger state

The GD30WS8815x device integrates a switching charger that allows the battery to be charged with a programmable charge current up to 1.5A. In addition to the charge current, other charging parameters can be also programmed through I2C such as the battery regulation voltage, pre-charge current. The device supports multiple battery regulation voltage regulation settings ( $V_{\text{CVCH}}$ ) and charge current ( $I_{\text{CCCH}}$ ) options to support multiple battery chemistries for single-cell applications. A full one-cell charger state diagram as shown in Figure 5-2 is implemented in the IC.



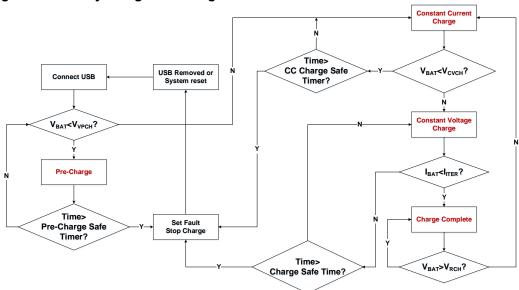


Figure 5-2 Battery charge state diagram

#### 5.2.2 Charge parameters

The maximum charge current is programmed by a resistor connected from the ISET pin to ground. The resistor value can be calculated as:

$$R_{CCCH} = \frac{10}{I_{CCCH}} \ k\Omega$$
 
$$I_{PCH} = \frac{I_{CCCH}}{10}$$
 
$$R_{IOFF} = \frac{500}{I_{IOFF}} k\Omega$$

Where the unit of  $I_{CCCH}$  is A, the unit of  $I_{IOFF}$  is mA. The charge current also varies in different charging stages constant current loop (CC), constant voltage loop (CV). During the charging process, all control loops are enabled and the one that is dominant takes control regulating the charge current as needed. The relevant charge parameters and control loops are defined as in Figure 5-3.



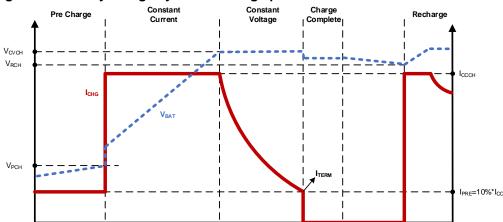


Figure 5-3 Battery charge cycle and charge parameters

The charger input has back to back blocking FETs to prevent reverse current flow from VBAT to VUSB. They also integrate control circuitry regulating the input current and prevents excessive currents from being drawn from the USB power supply for more reliable operation.

#### 5.3 Synchronous boost converter

The integrated synchronous boost converter is a wide input range, high-efficiency, DC-to-DC step-up switching regulator. It is capable of delivering up to 3W of output power, integrated with a  $150 \mathrm{m}\Omega$  high side PMOS and a  $150 \mathrm{m}\Omega$  low side NMOS. It uses a PWM current-mode control scheme. An error amplifier integrates error between the internal feedback signal proportional to VSYS and the internal reference voltage. The output of the integrator is then compared to the sum of a current-sense signal and the slope compensation ramp. This operation generates a PWM signal that modulates the duty cycle of the power MOSFETs to achieve regulation for output voltage.

Integrated VBAT to VSYS synchronous boost output function, the output voltage is 5V, which can be set to  $4.8V \sim 5.15V$  by I2C. The boost module integrates the current limiting function. When the load current is too large, the chip enters the cycle-by-cycle current limiting mode, limiting the peak inductor current to 2.0A, which can be configured to 1.6A/1.8A/2.0A/2.2A by I2C. At the same time, the output voltage starts to drop. When the output voltage drops to 4.3V, the short-circuit protection is triggered.

The boost module also integrates an overvoltage protection function. When the output voltage is higher than 5.5V, the overvoltage protection is triggered. When the voltage of the boost module drops below 2.8V during the working process of the booster module, the boost module is automatically closed and locked in the under voltage lockout state.

The boost regulator provides excellent stability over a wide range of output current and operates in DCM at light loads for excellent efficiency. The switching frequency is fixed at 1MHz to reduce the external inductor size. The boost regulator is disabled when USB voltage is detected to save power.



#### 5.4 Power path management

#### **5.4.1** Power path management

The device integrates advanced power path management and control that allows the device to provide power to the system while charging the battery even with low power adapters. The dynamic power path management is able to automatically balance the currents delivered to the system and battery charging.

The charging current can be set to  $I_{CCCH}$  through the off-chip resistor connected to the ISET pin, and the chip input current is limited to  $I_{CCCH}$  +0.5A by the input current limit switch. In the charging and discharging mode, the system discharge priority. There are two situations that will cause the charging current to drop.

- When the discharge current plus the rated charging is higher than I<sub>CCCH</sub> +0.5A, the dynamic path management loop automatically reduces the charging current to meet the discharge demand.
- 2) When the power supply capacity of the input adapter is lower than Iccch+0.5A, and the rated charging current plus the VSYS discharge current is greater than the power supply capacity of the adapter, the VSYS voltage will drop, as the VSYS voltage drops to 4.6V, the charging current will be reduced through the feedback loop.

The chip also integrates the charging current temperature modulation function, when the chip temperature exceeds 110 degrees Celsius, the charging current is automatically reduced.

The input current limit switch also integrates short-circuit protection and over-current protection. When the current in the input switch exceeds 3A, the over-current protection is triggered. When the VSYS voltage drops below 4V, the short-circuit protection is triggered, the system stops working, and the input switch is closed. The chip enters hiccup mode and restarts every 250ms to check whether the abnormality exists. If the abnormality is removed, the chip returns to normal operation

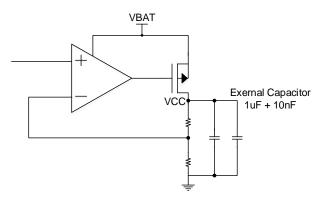
#### 5.4.2 LDO

A linear regulator is integrated to supply part of the chip and external circuits or MCU.

Output voltage of the LDO is 3.3V and the output driving current is 80mA.When output current exceeds 80mA, the output value will drop. When the chip works in sleep mode, LDO will enter low power mode to save power, which provides 10mA driving capability.



Figure 5-4 The principle diagram for LDO



#### 5.5 Earbud detection

The circuit detects the output current from EBL/EBR to show that earbud is inserted. EBL and EBR are independent channels which detect earbuds individually.

#### 5.6 NTC battery temperature

The GD30WS8815x chip integrates an NTC battery temperature protection circuit, which provides the over-temperature protection of high temperature 55°C and low temperature -10°C. The corresponding high and low temperature threshold voltages are respectively 30% and 60% of the input system voltage. When the battery temperature exceeds 55°C or fall below -10°C, the correlative high or low temperature output will be set high separately. If NTC pin is pulled down to GND, the NTC function is closed.

Figure 5-5 Diagram for the NTC circuit

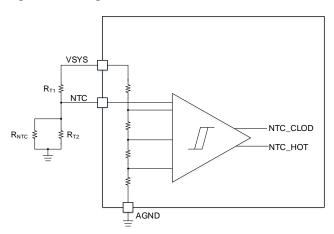


Table 5-1 Description of resistors for the NTC circuit

Symbol	Parameter	Typical value	Unit
R <sub>NTC</sub>	NTC thermistor	10	ΚΩ
R <sub>T1</sub>	Resistor for voltage division	5.23	ΚΩ
R <sub>T2</sub> Resistor for voltage division		9.31	ΚΩ



#### 5.7 LED driver

The chip supports 1-4 LED mode (see Table 5-2 to Table 5-5). The GD30WS8815x supports LED control by I2C (see Table 5-6toTable 5-8).

## 5.7.1 LED connection and display mode

Figure 5-6 1-LED Mode

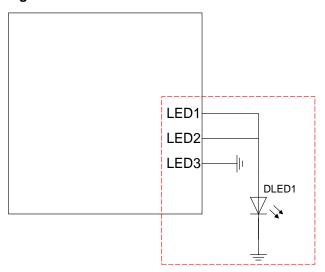


Table 5-2 1-LED Display Mode

Mode	Battery Status DLED1			
Charge	Full	Always On		
Charge	Charging	Blink at 1Hz		
Diagharga	Normal Power	On for 8s		
Discharge	Low Battery	Blink at 1Hz for 8s		
Earbud plug in	in — Blink at 1Hz for			

Figure 5-7 2-LED Mode

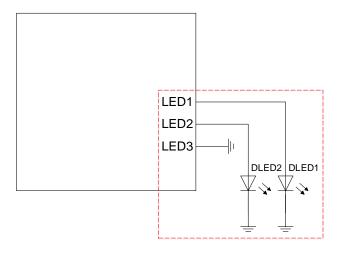
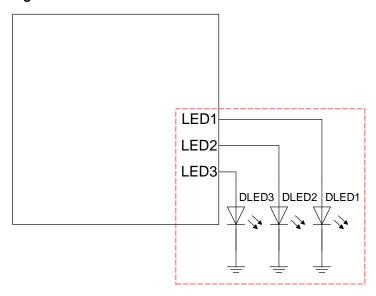




Table 5-3 2-LED Display Mode

Mode	Battery Status	DLED1	DLED2
Chargo	Full	Off	Always On
Charge	Charging	Off	Blink at 1Hz
Discharge	Normal Power	On for 8s	Off
Discharge	Low Battery	Blink at 1Hz for 8s	Off
Earbud plug in	_	Blink at 1H	Iz for 1s

Figure 5-8 3-LED Mode



**Table 5-4 3-LED Display Mode** 

Mode	Battery Level	DLED1	DLED2	DLED3
	Full	Always On	Always On	Always On
Charge	66%-100%	Always On	Always On	Blink at 1Hz
Charge	33%-66%	Always On	Blink at 1Hz	Off
	0%-33%	Blink at 1Hz	Off	Off
	66%-100%	On for 8s	On for 8s	On for 8s
Discharge	33%-66%	On for 8s	On for 8s	Off
Discharge	5%-33%	On for 8s	Off	Off
	0%-5%	Blink at 1Hz for 8s	Off	Off
Earbud plug in				



Figure 5-9 4-LED Mode

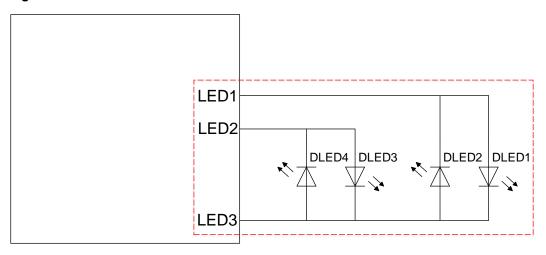


Table 5-5 4-LED Display Mode

Mode	Battery Level	DLED1	DLED2	DLED3	DLED4
	Full	Always On	Always On	Always On	Always On
	75%-100%	Always On	Always On	Always On	Blink at 1Hz
Charge	50%-75%	Always On	Always On	Blink at 1Hz	Off
	25%-50%	Always On	Blink at 1Hz	Off	Off
	0%-25%	Blink at 1Hz	Off	Off	Off
	75%-100%	On for 8s	On for 8s	On for 8s	On for 8s
	50%-75%	On for 8s	On for 8s	On for 8s	Off
Discharge	25%-50%	On for 8s	On for 8s	Off	Off
Discharge	5%-25%	On for 8s	Off	Off	Off
	0%-5%	Blink at 1Hz for 8s	Off	Off	Off
Earbud plug in		Blink at 1Hz for 1s			

## 5.7.2 LED Display Mode Configuration

**Table 5-6 LED Display Mode Register** 

Register Address	Bits	R/W	Fields	Description
				LED mode status, default: 2'b00
	d [2:1] RW LED_I2C_MDST	00: 2 LED Mode		
0x0d		01: 3 LED Mode		
				10: 1 LED Mode
				11: 4 LED Mode



#### **5.7.3** LED Driving Capability Configuration

**Table 5-7 LED Driving Register** 

Register Address	Bits	R/W	Fields	Description
				LED current set, default: 2'b10 00: 0.5 mA
0x04	[5:4]	RW	LED_DRV	01: 1 mA
				10: 2 mA
				11: 4 mA

## 5.7.4 LED Display Control by I2C

**Table 5-8 LED Control Register** 

Register Address	Bits	R/W	Fields	Description
				I2C control enable, default: 1'b0
0x0d	[0]	RW	LED_I2C_EN	0: LED hardware control
				1: LED I2C control
	[13:10]	RW	LED_I2C_ST	LED Status, default: 4'b0000
				[13]: LED4 Status (0: Off, 1: On)
0x0d				[12]: LED3 Status (0: Off, 1: On)
				[11]: LED2 Status (0: Off, 1: On)
				[10]: LED1 Status (0: Off, 1: On)

#### 5.8 Earbud communication

MCU supports up to 2M bidirectional communication with earbud by COML/R pin and EBL/R pin. There are two kinds of Earbud communication. One is through changing and reading COML/R pin level for communication, configure COM\_I2C\_SEL to 0 & COM\_MD1EN to 1. The other is to communicate through the I2C control register changes, configure COM\_I2C\_SEL to 1 & COM\_MD2EN to 1. The communication block diagram of COML and EBL is shown in Figure 5-10.



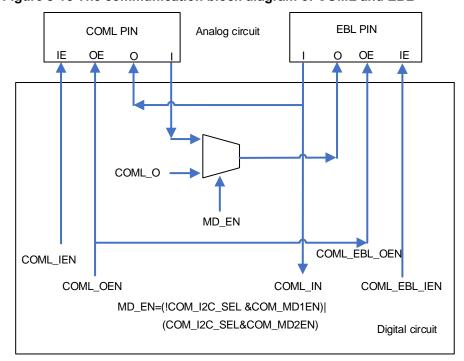


Figure 5-10 The communication block diagram of COML and EBL

When EBL/R is used as the output pin, the output low voltage is 0V, and the output high voltage is VBAT or 5V. (When boost is used, the output high voltage is 5V, otherwise the output high voltage is VBAT)

When COML/R is used as the output pin, the output low voltage is 0V, and the output high voltage is VBAT.

When EBL/R or COML/R is used as the input pins, the input low voltage is 0V - 0.35 \* VCC, and the input high voltage is 0.65 \* VCC - 5.5V. The input characteristics follow Table 6-5.

#### 5.9 EN and IRQ

The IRQ pin will generate a 8ms neg-edge pulse, when fault or work status are appeared. MCU can wake up the chip by giving a high voltage on EN pin.

IRQ sources include the following:

- 1) Battery charge end
- 2) Watch dog time out fault
- 3) Battery charge time out fault
- 4) Battery pre-charge time out fault
- 5) Over temperature fault (more than 150°C)
- 6) NTC Hot fault
- 7) NTC cold fault
- 8) VSYS under voltage fault
- 9) VSYS over voltage fault
- 10) USB plug in
- 11) USB pull out



- 12) Left or right earbud plug in
- 13) Left or right earbud pull out
- 14) Left or right earbud light load
- 15) Left or right earbud short/under voltage fault
- 16) VUSB over voltage fault
- 17) VBAT over voltage fault when charge the battery
- 18) VBAT under voltage fault when the battery discharge

#### 5.10 Over temperature protection

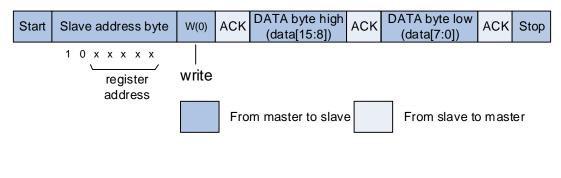
If the die temperature exceeds the trip point of the thermal shutdown limit  $(T_{SD})$ , all the circuits are disabled, and the IRQ pin is pulled low.

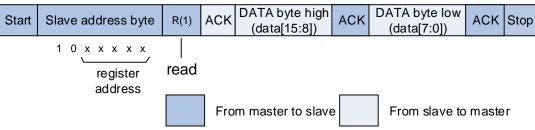
#### 5.11 I2C interface

The I2C (inter-integrated circuit) module provides an I2C interface which is an industry standard two-line serial interface for MCU to communicate with external I2C interface. I2C bus uses two serial lines: a serial data line (SDA), and a serial clock line (SCL).

The I2C interface implements standard I2C protocol with standard-mode (up to 100 kHz) and fast-mode (up to 400 kHz). The I2C interface only supports Slave-mode. The I2C interface receive data on rising SCL and transmit data on falling SCL.

Figure 5-11 I2C communication flow





The data format is fixed:

8bit function (2'b10 + 5bit(register address), +1bit(1'b0-write, 1'b1-read))

- + 8bit data[15:8]
- + 8bit data[7:0].



#### 5.12 ADC description

ADC has 8 conversion channels, and its VREF is 2.5V, which can be enabled through bit [11] of Control Register.

ADC can configure conversion channel through bits [3:1] of ADC Register.

The 0 conversion channel of ADC is battery voltage. Battery voltage with digital logic, earbud detection can achieve LED display function.

The 1, 2, 3 conversion channels of ADC are VRCH, VSENS\_EBL and VSEBS\_EBR, which can be used to detect the charging current of earbud. Take the left earbud as an example, the left earbud charging current can be calculated as:

$$I_{SW\_EBL} = \frac{20000 * VSENS\_EBL}{3 * VRCH * R_{CCCH}}$$

The maximum value of  $I_{SW\_EBL}$  can be set by bits [6:5] of User configure Register 3. When the calculated  $I_{SW\_EBL}$  is less than the maximum value, the earbud is in linear charging mode. When the calculated  $I_{SW\_EBL}$  is equal to the maximum value, the earbud is in current limiting charging mode

The 4, 5, 6 conversion channels of ADC are VCOM, VIC and VIR, which can be used to detect charging current. The ICCCH value can be calculated as:

$$I_{CCCH} = \frac{10000(VIC - VCOM)}{R_{CCCH}(VIR - VCOM)}$$

The 7 conversion channel of ADC is AVSS.

## 5.13 Register Map

#### 5.13.1 Fault Register

Address: 0b 00000

Bits	R/W	fields	default	Description
				I2C fault
4.5	D) //	IOC ACK FALILT		Software can clear it by writing 1.
15	RW	I2C_ACK_FAULT	0b0	0: I2C normally
				1: I2C ACK fault/clear
14	R	Reserved	0b0	Must be kept at reset value.
		PCH_TO_FAULT	0b0	Pre-charge timeout fault
				Software can clear it by writing Control Register bit10
13	R			I2C_CLR_FAULT.
				0: Pre-charge normally
				1: Pre-charge timeout fault



Bits	R/W	fields	default	Description
				Charge timeout fault
				Software can clear it by writing Control Register bit10
12	12 R	CH TO FAULT		I2C_CLR_FAULT.
		0.1101.10	0.20	 0: Charge normally
				1: Charge timeout fault
				Watchdog timeout fault
				Software can clear it by writing Control Register bit13
				WDG CLR or writing Watchdog Register bits
11	R	WDG_FAULT	0b0	WDG_DATA[9:1].
				0: Watchdog normally
				1: Watchdog timeout fault
				VUSB over current fault
10	R	VUSB_OC_FAULT	0b0	0: VUSB current normally
				1: VUSB over current fault
				VUSB over voltage fault
9	R	VUSB_OV_FAULT	0b0	0: VUSB voltage normally
	K VOOD_OV_TAGET		1: VUSB over voltage fault	
				EBR under voltage fault
				Software can clear it by writing Control Register bit10
8	R	EBR_UV_FAULT	0b0	I2C_CLR_FAULT.
				 0: EBR voltage normally
				1: EBR under voltage fault
				EBL under voltage fault
				Software can clear it by writing Control Register bit10
7	R	EBL_UV_FAULT	0b0	I2C_CLR_FAULT.
				0: EBL voltage normally
				1: EBL under voltage fault
				VSYS over voltage fault
				Software can clear it by writing Control Register bit10
6	R	VSYS_OV_FAULT	0b0	I2C_CLR_FAULT.
				0: VSYS voltage normally
				1: VSYS over voltage fault
				VSYS under voltage fault
				Software can clear it by writing Control Register bit10
5	R	VSYS_UV_FAULT	0b0	I2C_CLR_FAULT.
				0: VSYS voltage normally
				1: VSYS under voltage fault
				NTC_HOT fault
				Software can clear it by writing Control Register bit10
4	R	NTC_HOT_FAULT	0b0	I2C_CLR_FAULT.
				0: NTC normally
				1: NTC hot fault



Bits	R/W	fields	default	Description
				NTC_COLD fault
				Software can clear it by writing Control Register bit10
3	R	NTC_COLD_FAULT	0b0	I2C_CLR_FAULT.
				0: NTC normally
				1: NTC cold fault
				VBAT over voltage fault
				Software can clear it by writing Control Register bit10
2	R	VBAT_OV_FAULT	0b0	I2C_CLR_FAULT.
				0: VBAT voltage normally
				1: VBAT over voltage fault
				VBAT under voltage fault
				Software can clear it by writing Control Register bit10
1	R	VBAT_UV_FAULT	0b0	I2C_CLR_FAULT.
				0: VBAT voltage normally
				1: VBAT under voltage fault
				Over temperature fault
0	R	TEMP_FAULT	0b0	0: The battery temperature normally
				1: The battery over temperature fault

# 5.13.2 Status Register 1

Address: 0b 00001

Bits	R/W	fields	default	Description
				Pre-charge enable flag
15	R	PCH_ENF	0b0	0: Pre-charge is disabled
				1: Pre-charge is enabled
				VUSB enable flag
14	R	VUSB_ENF	0b0	0: VUSB is disabled
				1: VUSB is enabled
				VUSB over voltage detection enable flag
13	R	VUSBOV_ENF	0b0	0: VUSB over voltage detection is disabled
				1: VUSB over voltage detection is enabled
				VBAT pre-charge output flag
12	R	VBAT_PCH_OF	0b0	0: VBAT is higher than pre-charge threshold voltage VPCH
				1: VBAT is lower than pre-charge threshold voltage VPCH
				VBAT re-charge output flag
11	R	VBAT_RCH_OF	0b0	0: VBAT is higher than re-charge threshold voltage VRCH
				1: VBAT is lower than re-charge threshold voltage VRCH
				EBL enable flag
10	R	EBL_ENF	0b0	0: EBL is closed
				1: EBL is opened
9	R	EBR_ENF	0b0	EBR enable flag



Bits	R/W	fields	default	Description
				0: EBR is closed
				1: EBR is opened
8	R	Reserved	0b0	Must be kept at reset value.
				USB plug in flag
7	R	USB_PLINF	0b0	0: USB is not plugged in
				1: USB is plugged in
				Charge end flag
6	R	CH_ENDF	0b0	0: Charge is not ended
				1: Charge is ended
				Constant current charge end flag
5	R	CCCH_ENDF	0b0	0: Constant current charge is not ended
				1: Constant current charge is ended
				Left earbud plug in flag
4	R	EBL_PLINF	0b0	0: Left earbud is not plugged in
				1: Left earbud is plugged in
				Right earbud plug in flag
3	R	EBR_PLINF	0b0	0: Right earbud is not plugged in
				1: Right earbud is plugged in
				Left earbud current load flag
2	R	EBL_IOFFF	0b0	0: Heavy load
				1: Light load
				Right earbud current load flag
1	R	EBR_IOFFF	0b0	0: Heavy load
				1: Light load
				Boost enable flag
0	R	BST_ENF	0b0	0: Boost is disabled
				1: Boost is enabled

# 5.13.3 Status Register 2

Address: 0b 00010

Bits	R/W	fields	default	Description
15:8	R	Reserved	0b0	Must be kept at reset value.
				EBL under voltage detection enable flag
7	R	EBL_UVENF	0b0	0: EBL under voltage detection is disabled
				1: EBL under voltage detection is enabled
				EBR under voltage detection enable flag
6	R	EBR_UVENF	0b0	0: EBR under voltage detection is disabled
		,	1: EBR under voltage detection is enabled	
				Re-charge comparator enable flag
5	R	RCHCMP_ENF	0b0	0: Re-charge comparator is disabled
				1: Re-charge comparator is enabled



Bits	R/W	fields	default	Description
				VBAT over voltage detection enable flag
4	R	VBAT_OV_ENF	0b0	0: VBAT over voltage detection is disabled
				1: VBAT over voltage detection is enabled
3:2	R	Reserved	0b0	Must be kept at reset value.
				Pre- charge comparator enable flag
1	1 R PCHCMP_ENF	0b0	0: Pre-charge comparator is disabled	
				1: Pre-charge comparator is enabled
				Charge enable flag
0	R	CH_ENF	0b0	0: Charge is disabled
				1: Charge is enabled

# **5.13.4** Control Register

Address: 0b 00011

Bits	R/W	fields	default	Description
15	RW	Reserved	0b0	Must be kept at reset value.
				Temperature regulation enable
14	RW	TEMPREG_EN	0b0	0: Enable temperature regulation
				1: Disable temperature regulation
				Feed watchdog
				Software can clear it by writing 1 to this bit, or reset
13	RW	WDG_CLR	0b0	watchdog register bits WDG_DATA[9:1].
				0: Watchdog normally
				1: Feed watchdog
12	R	Reserved	0b0	Must be kept at reset value.
				ADC enable
11	RW	ADC_EN	0b0	0: Disable ADC
				1: Enable ADC
				I2C clear all faults
10	RW	I2C_CLR_FAULT	0b0	0: No effect
				1: Clear all faults
				Reset all chip
9	RW	RST_ALL	0b0	0: No effect
				1: Reset all chip
				Reset all chip but I2C itself
8	RW	RST_OTHS	0b0	0: No effect
				1: Reset all chip but I2C itself
				ADC clock selection
				00: ADC clock is 2MHz
7:6	RW	ADC_CLKSEL	0b0	01: ADC clock is 1MHz
				10: ADC clock is 500kHz
				11: ADC clock is 250kHz



Bits	R/W	fields	default	Description
5	R	Reserved	0b0	Must be kept at reset value.
				Boost enable
4	RW	BST_EN	0b0	0: Disable boost
				1: Enable boost
				Charge enable
3	RW	CH_EN	0b0	0: Disable charge
				1: Enable charge
				EBL switch enable
2	RW	EBL_EN	0b0	0: Close EBL
				1: Open EBL
				EBR switch enable
1	RW	EBR_EN	0b0	0: Close EBR
				1: Open EBR
				Sleep mode enable
0	RW	SLP_EN	0b0	0: Disable Sleep mode
				1: Enable Sleep mode

## 5.13.5 User configure Register 1

Address: 0b 00100

Bits	R/W	fields	default	Description
15:6	R	Reserved	0b0	Must be kept at reset value.
				LED current set
				00: 0.5 mA
5:4	RW	LED_DRV	0b10	01: 1 mA
				10: 2 mA
				11: 4 mA
				Boost maximum current threshold set
				00: Boost maximum current threshold 1.6A
3:2	RW	BST_ITHSET	0b10	01: Boost maximum current threshold 1.8A
				10: Boost maximum current threshold 2.0A
				11: Boost maximum current threshold 2.2A
				Earbud light load current set
				00: Earbud light load current is set to -10%
1:0	RW	IOFF_SET	0b10	01: Earbud light load current is set to -5%
				10: Earbud light load current is set to 0%
				11: Earbud light load current is set to +5%

## 5.13.6 User configure Register 2

Address: 0b 00101

Bits	R/W	fioldo	default	Description
DILO	IT./VV	tields	ueiauit	Description



Bits	R/W	fields	default	Description
15:13	R	Reserved	0b0	Must be kept at reset value.
				VSYS voltage set
				000: Boost output voltage 4.8V
				001: Boost output voltage 4.85V
				010: Boost output voltage 4.9V
12:10	RW	VSYS_SET	0b100	011: Boost output voltage 4.95V
				100: Boost output voltage 5V
				101: Boost output voltage 5.05V
				110: Boost output voltage 5.1V
				111: Boost output voltage 5.15V
				VUSB current limit set
				00: VUSB current limit is set to -5%
9:8	RW	VUSB_CL_SET	0b01	01: VUSB current limit is set to 0%
				10: VUSB current limit is set to +5%
				11: VUSB current limit is set to +10%
				Pre-charge current set
				00: Pre-charge current is set to 50%
7:6	RW	IPCH_SET	0b01	01: Pre-charge current is set to 100%
				10: Pre-charge current is set to 150%
				11: Pre-charge current is set to 150%
				Pre-charge terminate voltage set
				00: Pre-charge terminate voltage is 3.0V
5:4	RW	VPCHT_SET	0b01	01: Pre-charge terminate voltage is 3.1V
				10: Pre-charge terminate voltage is 3.2V
				11: Pre-charge terminate voltage is 3.3V
				Constant current charge current set
				00: Constant current charge current is set to 100%
3:2	RW	ICCCH_SET	0b0	01: Constant current charge current is set to 75%
				10: Constant current charge current is set to 50%
				11: Constant current charge current is set to 25%
				Re-charge threshold voltage set
				00: Re-charge threshold voltage is 3.9V
1:0	RW	VRCHT_SET	0b01	01: Re-charge threshold voltage is 4.0V
				10: Re-charge threshold voltage is 4.1V
				11: Re-charge threshold voltage is 4.2V

# 5.13.7 User configure Register 3

Address: 0b 00110

Bits	R/W	fields	default	Description
15:7	R	Reserved	0b0	Must be kept at reset value.
6:5	RW	EBLR_ILIM_SET	0b01	EBL/EBR limit current set



Bits	R/W	fields	default	Description
				00: 150mA
				01: 250mA
				10: 350mA
				11: 450mA
				Constant current charge terminate voltage set
				000: Constant current charge terminate voltage is 4.2V
4:2	RW			001: Constant current charge terminate voltage is 4.1V
		VCCCHT_SET		010: Constant current charge terminate voltage is 4.3V
				011: Constant current charge terminate voltage is 4.35V
				100: Constant current charge terminate voltage is 4.4V
				101: Constant current charge terminate voltage is 4.2V
				110: Constant current charge terminate voltage is 4.2V
				111: Constant current charge terminate voltage is 4.2V
				Charge terminate current set
				00: Charge terminate current minus 10mA
1:0	RW	ICHT_SET	0b10	01: Charge terminate current minus 5mA
				10: Charge terminate current no change
				11: Charge terminate current plus 5mA

# 5.13.8 Watchdog Register

Address: 0b 01011

Bits	R/W	Fields	default	Description	
15:10	R	Reserved	0b0	0b0 Must be kept at reset value.	
0.4	D) 4	14/DQ DATA	0x1ff	Watchdog counter set	
9:1	RW	WDG_DATA		Only set watchdog counter when WDG_EN is 0	
	0 RW WDG_EN		Watchdog enable		
0		WDG_EN		0: Disable watchdog	
				1: Enable watchdog	

# 5.13.9 COML/R Register

Address: 0b 01100

Bits	R/W	fields	default	Description
15	R	Reserved	0b0	Must be kept at reset value.
				EBL pin input enable
14	RW	COML_EBL_IEN	0b0	0: Disable EBL pin input
				1: Enable EBL pin input
				EBR pin input enable
13	RW	COMR_EBR_IEN	0b0	0: Disable EBR pin input
				1: Enable EBR pin input
12	RW	COML_IEN	0b0	COML pin input enable



Bits	R/W	fields	default	Description
				0: Disable COML pin input
				1: Enable COML pin input
				COMR pin input enable
11	RW	COMR_IEN	0b0	0: Disable COMR pin input
		_		1: Enable COMR pin input
				EBL pin output enable
10	RW	COML_EBL_OEN	0b0	0: Disable EBL pin output
				1: Enable EBL pin output
				EBR pin output enable
9	RW	COMR_EBR_OEN	0b0	0: Disable EBR pin output
				1: Enable EBR pin output
				Communication enable mode 2 I2C control
8	RW	COM_MD2EN	0b0	0: Disable mode 2
				1: Enable mode 2
				Communication enable mode 1 COML/R pin control
7	RW	COM_MD1EN	0b0	0: Disable mode 1
				1: Enable mode 1
				COML pin output enable
6	RW	COML_OEN	0b0	0: Disable COML pin output
				1: Enable COML pin output
				COMR pin output enable
5	RW	COMR_OEN	0b0	0: Disable COMR pin output
				1: Enable COMR pin output
				Communication selection
4	RW	COM_I2C_SEL	0b0	0: COML/R pin control
				1: I2C control
				COML pin input signal
3	R	COML_IN	0b0	0: COML pin input low
				1: COML pin input high
				COMR pin input signal
2	R	COMR_IN	0b0	0: COMR pin input low
				1: COMR pin input high
				COML pin output signal
1	RW	COML_O	0b0	0: COML pin output low
				1: COML pin output high
				COMR pin output signal
0	RW	COMR_O	0b0	0: COMR pin output low
				1: COMR pin output high

# 5.13.10 LED Register

Address: 0b 01101



Bits	R/W	fields	default	Description
15:14	R	Reserved	0b0	Must be kept at reset value.
				LED4 Status
13	RW	LED4_I2C_ST	0b0	0: Off
				1: On
				LED3 Status
12	RW	LED3_I2C_ST	0b0	0: Off
				1: On
				LED2 Status
11	RW	LED2_I2C_ST	0b0	0: Off
				1: On
				LED1 Status
10	RW	LED1_I2C_ST	0b0	0: Off
				1: On
9:3	R	Reserved	0b0	Must be kept at reset value.
				LED mode status
				00: 2 LED mode
2:1	RW	LED_I2C_MDST	0b0	01: 3 LED mode
				10: 1 LED mode
				11: 4 LED mode
				LED I2C control enable
0	RW	LED_I2C_EN	0b0	0: LED Hardware control
				1: LED I2C control

# 5.13.11 ADC Register

Address: 0b 01110

Bits	R/W	fields	default	Description
15:4	R	VBAT_VM	0b0	ADC measure VBAT 12 bit data.
3:1				ADC channel select
				000: Channel VBAT
	RW			001: Channel VRCH
		ADC_CHSEL		010: Channel VSENS_EBL
				011: Channel VSENS_EBR
				100: Channel VCOM
				101: Channel VIC
				110: Channel VIR
				111: Channel AVSS
0	R	Reserved	0b0	Must be kept at reset value.

# 5.13.12 DEBUG Register

Address: 0b 01111



Bits	R/W	fields	default	Description
				I2C/COML/COMR PAD filter enable.
15	RW	FIL_EN	0b0 0b0 0b0	0: Filter is disabled
				1: Filter is enabled
14:12	R	Reserved	0b0	Must be kept at reset value.
				Charge status timeout time select
	R/W			00: 120 minute
11:10		CH_TO_SEL	020	01: 180 minute
				10: 240 minute
				11: 60 minute
				Battery is charged fully, set by software. It will affect the
		VBAT_FULL	0b0	LED display
	D 44/			0: Battery is not charged fully. LED displays normally
9	R/W			according to battery power
				1: Battery is charged fully. LED displays according to
				battery full charge
8:0	R	Reserved	0b0	Must be kept at reset value.



#### 6 Electrical characteristics

#### 6.1 Absolute maximum ratings

The maximum ratings are the limits to which the device can be subjected without permanently damaging the device. Note that the device is not guaranteed to operate properly at the maximum ratings. Exposure to the absolute maximum rating conditions for extended periods may affect device reliability.

Table 6-1 Absolute maximum ratings

Symbol	Parameter	Min	Max	Unit					
Vusa	Power supply pin from USB other 5V input	-0.3	20	V					
$V_{BAT}$	Battery voltage	-0.3	7	V					
V <sub>SYS</sub>	Output Voltage	-0.3	7	V					
Vcc	LDO output voltage and Internal logic voltage	-0.3	7	V					
V <sub>IO</sub>	I/O pin voltage (LEDx, ISET, EN, NTC, SCL, SDA)	-0.3	7	V					
V <sub>EBLR</sub>	Earbuds positive terminal voltage (EBL/EBR)	-0.3	7	V					
Vsw	Switching node voltage (SW)	-0.3	7	V					
	Thermal characteristics								
TJ	Operating junction temperature	-40	150	°C					
T <sub>stg</sub>	Storage temperature	-65	150	°C					

## 6.2 Recommended operation conditions

**Table 6-2 Recommended operation conditions** 

Symbol	Parameter	Min	Тур	Max	Unit
Vusa	Power supply pin from USB other 5V input	4.4	5.0	5.5	V
V <sub>BAT</sub>	Battery voltage	2.2	4.0	4.4	V
Vsys	BOOST output Voltage	4.8	5.0	5.15	V
Vcc	LDO output voltage and Internal logic voltage	2.0	3.3	3.6	V
Thermal characteristics					
T <sub>A</sub>	Operating ambient temperature	-20	_	85	°C



#### 6.3 Electrical sensitivity

The device is strained in order to determine its performance in terms of electrical sensitivity. Electrostatic discharges (ESD) are applied directly to the pins of the sample.

**Table 6-3 Electrostatic Discharge characteristics** 

Symbol	Parameter	Conditions	Value	Unit
	Electrostatic discharge	T <sub>A</sub> = 25 °C;	13000	\/
Vesd(HBM)	voltage (human body model)	JS-001-2017	±2000	V
Vesd(CDM)	Electrostatic discharge	T <sub>A</sub> = 25 °C;	.1000	\/
	voltage (charge device model)	JS-002-2018	±1000	V

#### 6.4 Power supplies voltages and currents

Table 6-4 Power supplies voltages and currents

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
lα	Sleep mode quiescent current	V <sub>BAT</sub> = 5 V, T <sub>A</sub> = 25 °C		_	5.0	μΑ
ton	Turn-on time	V <sub>USB</sub> > V <sub>UVLO</sub> to outputs ready	5.0	_	-	ms
Vcc	VCC regulator voltage	$I_{VCC} = 0 \text{ to } 80 \text{ mA } (V_{BAT} > 3.4 \text{ V})$	3.1	3.3	3.5	V

## 6.5 Logic input characteristics

Table 6-5 Logic input characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
VIL	Input logic low voltage	_	0	_	0.35 * Vcc	V
V <sub>IH</sub>	Input logic high voltage	_	0.65 * V <sub>CC</sub>	_	5.5	V
V <sub>HYS</sub>	Input logic hysteresis	_	100		_	mV

## 6.6 Open drain outputs characteristics

Open drain output pins include SCL, SDA, IRQ.

Table 6-6 Open drain output characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Vol	Output logic low voltage	Io = 5 mA	_	_	0.1	V
loz	Output high impedance leakage	$V_O = V_{BAT}$	-2	_	2	μΑ



#### 6.7 NTC characteristics

**Table 6-7 NTC characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>TL</sub>	Low Temperature threshold voltage			0.6 * V <sub>SYS</sub>		V
V <sub>TH</sub>	High Temperature threshold voltage	_	_	0.3 * V <sub>SYS</sub>	_	V
V <sub>offset</sub>	Offset Volatage				5	mV

## 6.8 Switching charger characteristics

**Table 6-8 Charger characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
.,	CV Charge voltage	Programmable	4.1	4.2	4.4	V
V <sub>CVCH</sub>	CV Charge voltage precision	_	_	0.5	_	%
Ісссн	CC Charge current	$R_{CCCH} = 20 \text{ K}\Omega$	_	0.5	_	Α
I <sub>PCH</sub>	Pre-Charge current	R <sub>CCCH</sub> = 20 KΩ	40	50	60	mA
I <sub>TER</sub>	Charge terminate current	_	I <sub>PCH</sub> + 10			mA
V <sub>PCH</sub>	Pre-Charge to CC charge transition	Programmable	_	3.0	_	V
V <sub>PCHHYS</sub>	Pre-Charge hysteresis voltage	_	_	200	_	mV
V <sub>RCH</sub>	Re-Charge threshold	_	_	4	_	V
V <sub>RCHHYS</sub>	Re-Charge hysteresis voltage		_	200	_	mV

Figure 6-1 Constant current charging efficiency

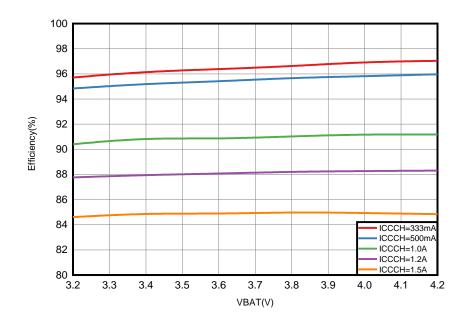




Figure 6-2 Constant current charging chip case temperature

Charge Time (S)
Icc = 500mA, Ta = 25°C

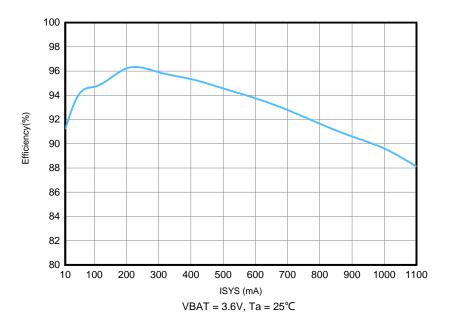
#### 6.9 Boost converter characteristics

**Table 6-9 Boost converter characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BAT</sub>	Operation battery voltage	_	3.0	3.7	4.5	V
$V_{BATLOW}$	Minimum battery	I <sub>SYS</sub> = 1 A	2.9	_	_	V
I <sub>BAT</sub>	Boost operation current	$V_{BAT} = 3.7 V$	_	4.0	6.0	mA
Vsys	Output voltage	$I_{SYS} = 0 \text{ mA}$	4.90	5.05	5.15	V
VSYS	Output voltage	I <sub>SYS</sub> = 1 A	4.80	5.00	5.15	V
$\Delta V_{SYS}$	Output ripple	_	_	100	_	mV
I <sub>SYS</sub>	Output current	_	_	_	1	Α
R <sub>HS</sub>	High Side PMOS on resistance	V <sub>CC</sub> = 3.3 V, T <sub>A</sub> = 25 °C	_	150	_	mΩ
R <sub>LS</sub>	Low Side NMOS on resistance	V <sub>CC</sub> = 3.3 V, T <sub>A</sub> = 25 °C	_	150	_	mΩ
l	Peak current limit	V <sub>BAT</sub> = 3.7 V, T <sub>A</sub> = 25 °C	_	2.0	_	Α
ILIM	Peak current limit during startup	V <sub>BAT</sub> = 3.7 V, T <sub>A</sub> = 25 °C	_	0.6	_	Α
f <sub>SW</sub>	Switching frequency	_	0.9	1.0	1.1	MHz
Isw	Switching node leakage	_	_	_	1.0	uA
D <sub>max</sub>	Maximum Duty Cycle	_	90	_	_	%



Figure 6-3 BOOST conversion efficiency



### 6.10 ADC characteristics

**Table 6-10 ADC characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>BAT</sub>	Operation battery voltage	_	3.0	3.7	4.5	V
f <sub>ADC</sub>	ADC clock frequency	_	_	2.0	_	MHz
fs	Sampling rate			0.08	1	MSPS
$V_{REFP}$	Positive Reference Voltage		2.49	2.5	2.51	V
V <sub>REFN</sub>	Negative Reference Voltage	_	_	0	_	V
	0 1: 1:	f 2 MLI=	_	6	_	us
t <sub>s</sub>	Sampling time f <sub>ADC</sub> = 2 MHz		_	12	_	1/ f <sub>ADC</sub>
toovii	Total conversion time(including			25		1/ f <sub>ADC</sub>
tconv	sampling time)	_		23	_	17 IADC
<b>t</b> STAB	Power-up time			_	1	us
ENOB	Effective number of bits	f <sub>ADC</sub> = 2 MHz	_	10.3	_	bits
SNDR	Signal-to-noise and distortion ratio	Input Frequency = 2	_	63.8	_	
SNR	Signal-to-noise ratio	kHz	_	64.5	_	dB
THD	Total harmonic distortion	Temperature = 25 °C	_	-71.0	_	
Offset	Offset error fanc = 2 MHz		±1	_	_	- LSB
DNL	Differential linearity error	IADC – Z IVITIZ	±1.5	_	_	LOD



## 6.11 Timing characteristics

**Table 6-11 Timing characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
tpch_fault	Pre-charge fault time	_	_	30	_	min
t <sub>CH_TO</sub>	Charge Time Out	_	_	180	_	min

## 6.12 Earbud Output Switch characteristics

Table 6-12 Earbud output switch characteristics

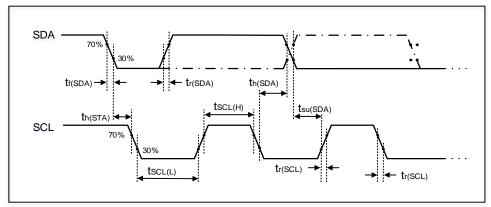
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ILIM	EBL/EBR output current Limit (Default)	V <sub>BAT</sub> = 3.0 ~ 4.2 V	_	250	_	mA
V <sub>SHORT</sub>	Short protect voltage	_	_	4.3	_	V
R <sub>switch</sub>	Switch resistance	V <sub>SYS</sub> = 5 V	_	400	_	mΩ
I <sub>DET_EAR</sub>	Earbud detected current threshold	_	5	_	_	uA

#### 6.13 I2C characteristics

Table 6-13 I2C characteristics

			Standard mode		Fast mode		
Symbol	Parameter	Conditions	Min	Max	Min	Max	Unit
t <sub>SCL(H)</sub>	SCL clock high time	_	4.0	_	0.6	_	μs
t <sub>SCL(L)</sub>	SCL clock low time		4.7		1.3	-	μs
t <sub>su(SDA)</sub>	SDA setup time	_	250	-	100	_	ns
t <sub>h(SDA)</sub>	SDA data hold time	_	0	3450	0	900	ns
t <sub>r(SDA/SCL)</sub>	SDA and SCL rise time	_	_	1000	_	300	ns
t <sub>f(SDA/SCL)</sub>	SDA and SCL fall time		_	300	3	300	ns
t <sub>h(STA)</sub>	Start condition hold time	_	4.0	_	0.6	_	μs

Figure 6-4 I2C bus timing diagram





### 6.14 Protection features

Protection features include over current protection, under voltage, over voltage and thermal shutdown.

**Table 6-14 Protection features characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
-		V <sub>USB</sub> Switch				
V <sub>USB_UVP</sub>	V <sub>USB</sub> under voltage Protection Threshold	Vusa falling —		4.3	_	٧
Vusb_ovp	V <sub>USB</sub> over voltage Protection Threshold	V <sub>USB</sub> rising	_	5.6	_	<b>V</b>
$I_{USB\_Limit}$	V <sub>USB</sub> input current limit	_	_	0.5 + I <sub>CCCH</sub>	_	Α
$V_{\text{SYS\_short}}$	V <sub>SYS</sub> short voltage Protection Threshold	Vsys falling	_	4.0	_	٧
		Charge	<u>'</u>			
		VCCCHT_SET = 000	_	4.3	_	
		VCCCHT_SET = 001	_	4.2	_	
		VCCCHT_SET = 010	_	4.4	_	
	V <sub>BAT</sub> over voltage	VCCCHT_SET = 011	_	4.45	_	.,
$V_{BAT\_OVP}$	Protection Threshold	VCCCHT_SET = 100	_	4.5	_	V
		VCCCHT_SET = 101	_	4.3	_	
		VCCCHT_SET = 110	_	4.3	_	
		VCCCHT_SET = 111	_	4.3	_	
V <sub>SYS_DPM</sub>	V <sub>SYS</sub> voltage regulation limit	_	_	4.6	_	V
		Boost				
V <sub>BAT_UVP</sub>	V <sub>BAT</sub> under voltage Protection Threshold	V <sub>BAT</sub> Falling	_	2.8		٧
VBATUVP_HSY	V <sub>BAT</sub> under voltage Protection hysteresis	_	_	0.1	_	٧
Vsys_short	V <sub>SYS</sub> short Protection Threshold	_	_	4.3	_	٧
V <sub>SYS_OVP</sub>	V <sub>SYS</sub> over voltage Protection Threshold	_	_	5.5	_	٧
Earbud Output Switch						
		EBLR_ILIM_SET = 00		150		mA
I.	EDI /EDD output ourrant limit	EBLR_ILIM_SET = 01	_	250	_	mA
I <sub>LIM</sub>	EBL/EBR output current Limit	EBLR_ILIM_SET = 10	_	350	_	mA
		EBLR_ILIM_SET = 11	_	450	_	mA
Iclose	EBL/EBR light load Protection current	R <sub>close</sub> = 50 KΩ	_	10	_	mA
V <sub>short</sub>	EBL/EBR short	_	_	4.3	_	V



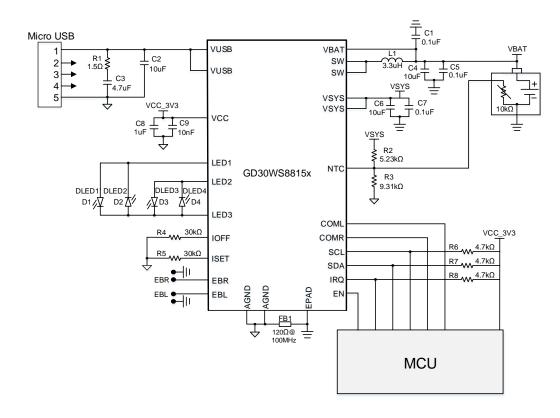
## GD30WS8815x Datasheet

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
	Protection Threshold							
Temperature								
Тот	Thermal shutdown temperature	Die temperature, T₃	_	150	_	°C		
T <sub>HYS</sub>	Thermal hysteresis	Die temperature, T <sub>J</sub>	_	20	_	°C		



## 7 Typical application circuit

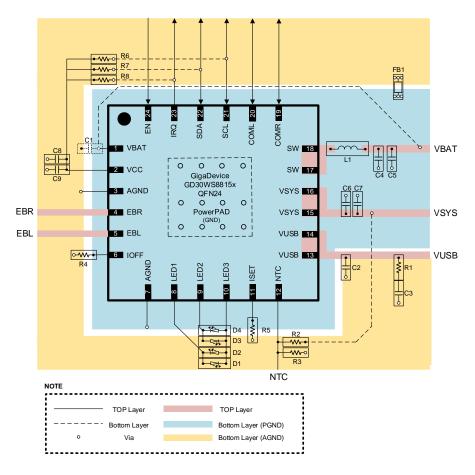
Figure 7-1 Typical GD30WS8815x application circuit





## 8 Layout guideline

Figure 8-1 Typical GD30WS8815x layout guideline



#### Notes:

- The VBAT C1 bypass capacitor should be connected to AGND to ensure the stability of the analog loop. The VBAT C4 and C5 bypass capacitors should be connected to PGND to ensure the stability of the power loop.
- 2. The SW L1 inductor should be as close to the pin as possible to reduce parasitic parameters.
- 3. The VSYS C6 and C7 bypass capacitor should be as close to the pin as possible to ensure the stability of the output power supply.



# 9 Package information

## 9.1 QFN24 package information

Figure 9-1 QFN24 package outline

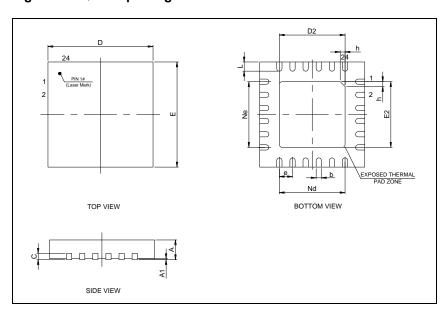


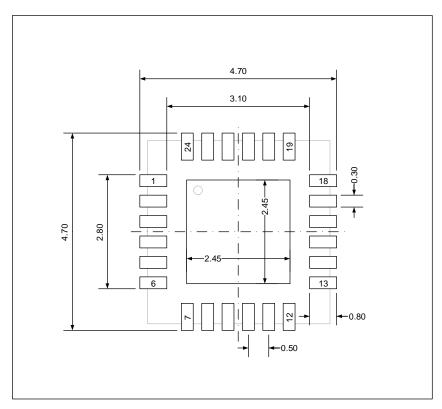
Table 9-1 QFN24 dimensions

Symbol	Min	Тур	Max
A	0.70	0.75	0.80
A1	_	0.02	0.05
b	0.18	0.25	0.30
С	0.18	0.20	0.25
D	3.90	4.00	4.10
D2	2.40	2.50	2.60
Е	3.90	4.00	4.10
E2	2.40	2.50	2.60
е	_	0.50	_
h	0.30	0.35	0.40
L	0.35	0.40	0.45
Nd	_	2.50	_
Ne	_	2.50	_

(Original dimensions are in millimeters)



Figure 9-2 QFN24 recommended footprint



(All dimensions are in millimeters)



#### 9.2 Thermal characteristics

Thermal resistance is used to characterize the thermal performance of the package device, which is represented by the Greek letter "O". For semiconductor devices, thermal resistance represents the steady-state temperature rise of the chip junction due to the heat dissipated on the chip surface.

Θ<sub>JA</sub>: Thermal resistance, junction-to-ambient.

Θ<sub>JB</sub>: Thermal resistance, junction-to-board.

Θ<sub>JC</sub>: Thermal resistance, junction-to-case.

Ψ<sub>JB</sub>: Thermal characterization parameter, junction-to-board.

 $\Psi_{JT}$ : Thermal characterization parameter, junction-to-top center.

 $\Theta_{JA} = (T_J - T_A)/P_D$ 

 $\Theta_{JB} = (T_J - T_B)/P_D$ 

 $\Theta_{JC} = (T_J - T_C)/P_D$ 

Where,  $T_J$  = Junction temperature.

 $T_A$  = Ambient temperature

T<sub>B</sub> = Board temperature

T<sub>C</sub> = Case temperature which is monitoring on package surface

P<sub>D</sub> = Total power dissipation

 $\Theta_{JA}$  represents the resistance of the heat flows from the heating junction to ambient air. It is an indicator of package heat dissipation capability. Lower  $\Theta_{JA}$  can be considerate as better overall thermal performance.  $\Theta_{JA}$  is generally used to estimate junction temperature.

 $\Theta_{JB}$  is used to measure the heat flow resistance between the chip surface and the PCB board.

 $\Theta_{JC}$  represents the thermal resistance between the chip surface and the package top case.  $\Theta_{JC}$  is mainly used to estimate the heat dissipation of the system (using heat sink or other heat dissipation methods outside the device package).

Table 9-2 Package thermal characteristics(1)

Symbol	Condition	Package	Value	Unit
ОЈА	Natural convection, 2S2P PCB	QFN24	47.51	°C/W
ΘЈВ	Cold plate, 2S2P PCB	QFN24	14.9	°C/W
Θιс	Cold plate, 2S2P PCB	QFN24	20.99	°C/W
$\Psi_{JB}$	Natural convection, 2S2P PCB	QFN24	15.05	°C/W
$\Psi_{JT}$	Natural convection, 2S2P PCB	QFN24	0.86	°C/W

<sup>(1)</sup> Thermal characteristics are based on simulation, and meet JEDEC specification.



# 10 Ordering information

Table 10-1 Part ordering code for GD30WS8815x devices

Ordering Code	Package	Package Type	Packing Type	MOQ	Temperature Operating Range
GD30WS8815EUTR	QFN24(4X4)	Green	Tape&Reel	3000	–20°C to +85°C



# 11 Revision history

Table 11-1 Revision history

Revision No.	Description	Date		
1.0	Initial Release	2022		
	1.Section 4.1 Part Order Code is modified to Part Number.			
	2.The Package description in section 4.1 is modified to			
	QFN24(4X4).			
1.1	3.The Ordering Code content in Chapter 10 is modified to	2022		
	GD30WS8815EUTR.			
	4.Chapter 10 Ordering information added information on			
	Packing Type(Tape&Reel) and MOQ(3000).			



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